



**IN THE UNITED STATES PATENT AND TRADEMARK OFFICE**

In re the Application of: **Masayuki FURUHASHI et al.**

Group Art Unit: **2813**

Application Number: **10/696,775**

Examiner: **Stephen W. Smoot**

Filed: **October 30, 2003**

Confirmation Number: **7971**

**For: METHOD FOR FABRICATING A SEMICONDUCTOR DEVICE  
INCLUDING THE USE OF A COMPOUND CONTAINING SILICON  
AND NITROGEN TO FORM AN INSULATION FILM OF SiN, SiCN OR  
SiOCN (as herein amended)**

Attorney Docket Number: **032076**  
Customer Number: **38834**

**AMENDMENT UNDER 37 C.F.R. § 1.111**

Commissioner for Patents  
P. O. Box 1450  
Alexandria, VA 22313-1450

September 16, 2005

Sir:

In response to the Office Action dated May 16, 2005, the response date of which having been extended by one month to September 16, 2005, Applicants amend the claims as follows and submit the following remarks.

Amendments to the Specification begin on page 2 of this paper.

Amendments to the Claims begin on page 3 of this paper.

Remarks begin on page 13 of this paper.